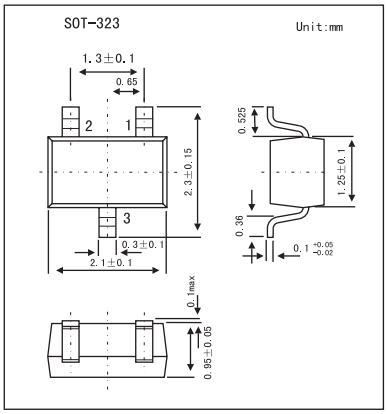
Silicon Schottky Barrier Diode

HSB276S



■ Features

- High forward current, Low capacitance.
- HSB276S which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	3	V
Average rectified current	I_O	30	mA
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F =1.0 mA	3			V
Reverse current	I_R	V_R =0.5 V			50	μA
Forward current	I_F	V_F =0.5 V	35			mA
Capacitance	C	V_R = 0.5 V, f = 1 MHz			0.90	pF
Capacitance deviation	ΔC	V_R = 0.5V, f = 1 MHz			0.10	pF
ESD-Capability (Note 1)		C=200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geqslant 100$ μA at V_R =0.5 V

■ Marking

Marking	C2